

John Marsland

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of RTN on Pattern Recognition Accuracy of RRAM-Based Synaptic Neural Network. IEEE Electron Device Letters, 2018, 39, 1652-1655.	3.9	38
2	Dependence of Switching Probability on Operation Conditions in Ge _x Se _{1-x} Ovonic Threshold Switching Selectors. IEEE Electron Device Letters, 2019, 40, 1269-1272.	3.9	23
3	As-grown-Generation Model for Positive Bias Temperature Instability. IEEE Transactions on Electron Devices, 2018, 65, 3662-3668.	3.0	22
4	The Over-Reset Phenomenon in Ta ₂ O ₅ RRAM Device Investigated by the RTN-Based Defect Probing Technique. IEEE Electron Device Letters, 2018, 39, 955-958.	3.9	18
5	GeSe-Based Ovonic Threshold Switching Volatile True Random Number Generator. IEEE Electron Device Letters, 2020, 41, 228-231.	3.9	17
6	Random-telegraph-noise-enabled true random number generator for hardware security. Scientific Reports, 2020, 10, 17210.	3.3	12
7	TDDB Mechanism in a-Si/TiO ₂ Nonfilamentary RRAM Device. IEEE Transactions on Electron Devices, 2019, 66, 777-784.	3.0	10
8	Cycling Induced Metastable Degradation in GeSe Ovonic Threshold Switching Selector. IEEE Electron Device Letters, 2021, 42, 1448-1451.	3.9	10
9	Bias Temperature Instability of MOSFETs: Physical Processes, Models, and Prediction. Electronics (Switzerland), 2022, 11, 1420.	3.1	6
10	RTN in Ge _x Se _{1-x} OTS selector devices. Microelectronic Engineering, 2019, 215, 110990.	2.4	3
11	Stochastic Computing Based on Volatile GeSe Ovonic Threshold Switching Selectors. IEEE Electron Device Letters, 2020, 41, 1496-1499.	3.9	3